This GIDEP PCN is to announce a change in the Electrical Characteristic for the N-Channel device of the following International Rectifier Part No.

**IRHMS57Z60**
30V Single N-Channel TID Hardened MOSFET in a TO-254AA

1. Change RDS(on) Static Drain-to-Source On-State maximum limit from 0.0045 Ω to 0.0055 Ω @ VGS = 12V, ID = 45A and Tj = 25°C

2. Change RDS(on) Static Drain-to-Source On-State maximum limit for Post Total Dose Irradiation characteristics from 0.0045 Ω to 0.0055 Ω @ VGS = 12V, ID = 45A and Tj = 25°C for up to 600K Rads and from 0.0050 Ω to 0.0060 Ω @ VGS = 12V, ID = 45A and Tj = 25°C for up to 1,000K Rads

3. Update SOA graph

**IR Part Numbers:**
- IRHMS57Z60 (100K Rads (Si) 0.0045Ω 45A)
- IRHMS53Z60 (300K Rads (Si) 0.0045Ω 45A)
- IRHMS54Z60 (600K Rads (Si) 0.0045Ω 45A)
- IRHMS58Z60 (1000K Rads (Si) 0.0045Ω 45A)

Reference: IR Datasheet PD-96961